

L Number	Hits	Search Text	DB	Time stamp
1	35209	330/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 13:25
2	1582	330/\$.ccls. and (high-voltage (high ADJ voltage))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:20
3	1295	(330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 13:26
4	1290	((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:54
5	1191	((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:54
6	1114	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:56
7	32	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (gate ADJ oxide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:55
8	272	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and MOS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:53
9	24	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and MOS) and (gate ADJ oxide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:08
10	1	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (LOCOS ADJ oxide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:56
11	13	5973368.URPN.	USPAT	2003/01/15 14:10
12	293	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and swing	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:19
13	84	(((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (mirror NEAR transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:19
14	12728	(257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:52
15	5277	((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:17
16	3374	((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:54

17	990	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:55
18	475	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:55
19	115	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:56
20	115	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and (gate source drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 14:57
21	113	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and (width length thick\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:08
22	1	5933731.URPN.	USPAT	2003/01/15 16:01
23	12	("4378565" "4525811" "4651406" "5241208" "5254489" "5400278" "5436495" "5472892" "5502009" "5663084" "5712178" "5712201").PN.	USPAT	2003/01/15 16:03
24	0	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and MEMS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:09
25	3	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and MEMS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:13
26	6	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and MEMS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:14
27	0	(((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:14
28	1	((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:15
29	2	((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:16
30	0	((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:16
31	0	((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:16
32	0	((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:16
33	0	(330/\$.ccls. and (high-voltage (high ADJ voltage))) and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:17

34	0	330/\$.ccls. and (MEMS NEAR mirror)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:17
35	276	MEMS NEAR mirror	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:17
36	12	(MEMS NEAR mirror) and MOS	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:17
37	19	(MEMS NEAR mirror) and (high-voltage (high ADJ voltage))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/01/15 16:20